

In the Claims

Claim 1 (canceled).

Claim 2 (Previously presented): The semiconductor package of claim 7 wherein the dielectric support member is a photomask material.

Claim 3 (Previously presented): The semiconductor package of claim 7 wherein the dielectric support member is not a photomask material.

Claim 4 (Previously presented): The semiconductor package of claim 7 wherein the one or more circuit traces comprise copper.

Claims 5 and 6 (canceled).

Claim 7 (Previously presented): A semiconductor package, comprising:

- an interposer construction containing only a single dielectric support member and comprising a plurality of conductive circuit traces contacting the single dielectric support member;
- a semiconductor die electrically connected with at least one of the circuit traces;
- at least one of the circuit traces being between the semiconductor die and the dielectric support member;
- the dielectric support member having a first surface and an opposing second surface, the plurality of the circuit traces being over the first surface, openings extending through the second surface to at least some of the circuit traces;
- contact pads within one or more of the openings and in electrical connection with one or more of the circuit traces, the contact pads being entirely contained within the openings wherein an entirety of at least one of the contact pads is elevationally spaced from at least one of the first and the second surfaces of the dielectric support member; and
- solder balls in electrical connection with the contact pads.

Claim 8 (Previously presented): The semiconductor package of claim 7 wherein:

- the dielectric support member has a slit extending therethrough; and
- the electrical connection of the semiconductor die to said at least one of the circuit traces includes one or more wire bonds extending from the die, through the slit, and into at least one of the openings.

Claims 9-56 (canceled).

Claim 57 (Previously presented): The semiconductor package of claim 7 wherein the entirety of the at least one contact pad is elevationally spaced from the first surface of the dielectric support member.

Claim 58 (Previously presented): The semiconductor package of claim 7 wherein the entirety of the at least one contact pad is elevationally spaced from the second surface of the dielectric support member.

Claim 59 (Previously presented): The semiconductor package of claim 7 wherein the entirety of the at least one contact pad is elevationally spaced from both of the first and the second surfaces of the dielectric support member.

Claim 60 (Previously presented): The semiconductor package of claim 7 further comprising an adhesive structure directly contacting the plurality of the circuit traces and directly contacting the semiconductor die, the adhesive structure comprising dielectric material.

Claim 61 (Previously presented): The semiconductor package of claim 7 wherein the at least one contact pad comprises at least two conductive layers.

Claim 62 (New): The semiconductor package of claim 7 wherein the interposer construction has a thickness, and wherein the thickness comprises a range from about 15 micrometers to about 150 micrometers.

Claim 63 (New): The semiconductor package of claim 7 wherein the interposer construction has a thickness, and wherein the thickness comprises about 50 micrometers.

Claim 64 (New): The semiconductor package of claim 7 wherein the single dielectric support member comprises at least one of polyimide and liquid polymer crystal.

Claim 65 (New): The semiconductor package of claim 7 further comprising an adhesive structure directly contacting the single dielectric support member and directly contacting the semiconductor die, the adhesive structure comprising dielectric material.